## Silicon P-Channel MOS FET

# HITACHI

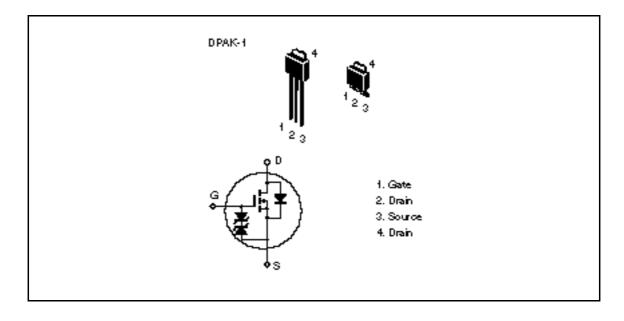
### **Application**

High speed power switching

#### **Features**

- · Low on-resistance
- High speed switching
- · Low drive current
- · No secondary breakdown
- Suitable for switching regulator and DC-DC converter

#### **Outline**





## Absolute Maximum Ratings ( $Ta = 25^{\circ}C$ )

Item	Symbol	Ratings	Unit	
Drain to source voltage	$V_{ t DSS}$	-600	V	
Gate to source voltage	$V_{\sf GSS}$	±15	V	
Drain current	I <sub>D</sub>	-0.5	Α	
Drain peak current	I *1 D(pulse)	-1.0	А	
Body to drain diode reverse drain current	I <sub>DR</sub>	-0.5	А	
Channel dissipation	Pch*2	20	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

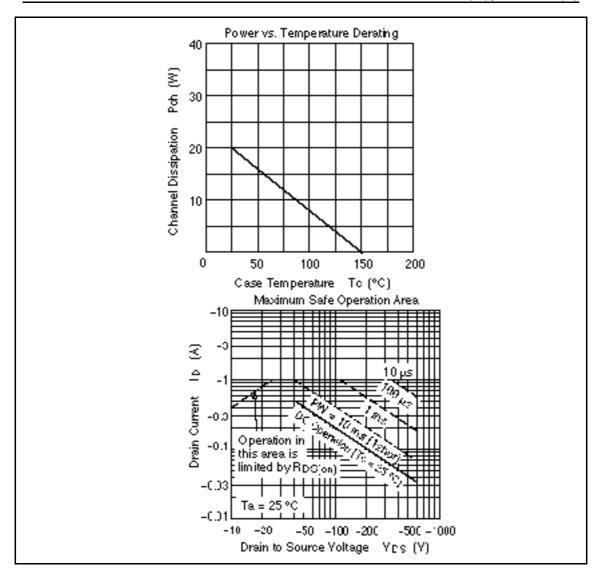
Notes: 1. PW 10 µs, duty cycle 1%

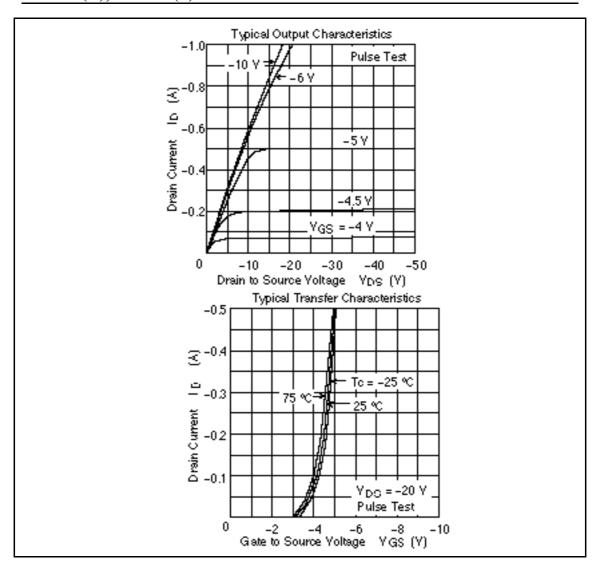
2. Value at  $T_c = 25$ °C

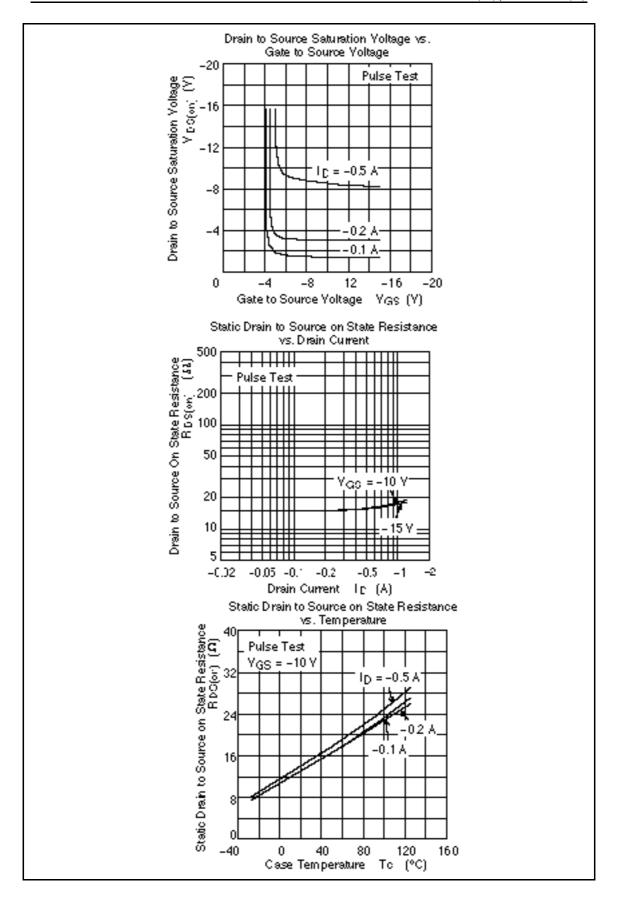
### **Electrical Characteristics** ( $Ta = 25^{\circ}C$ )

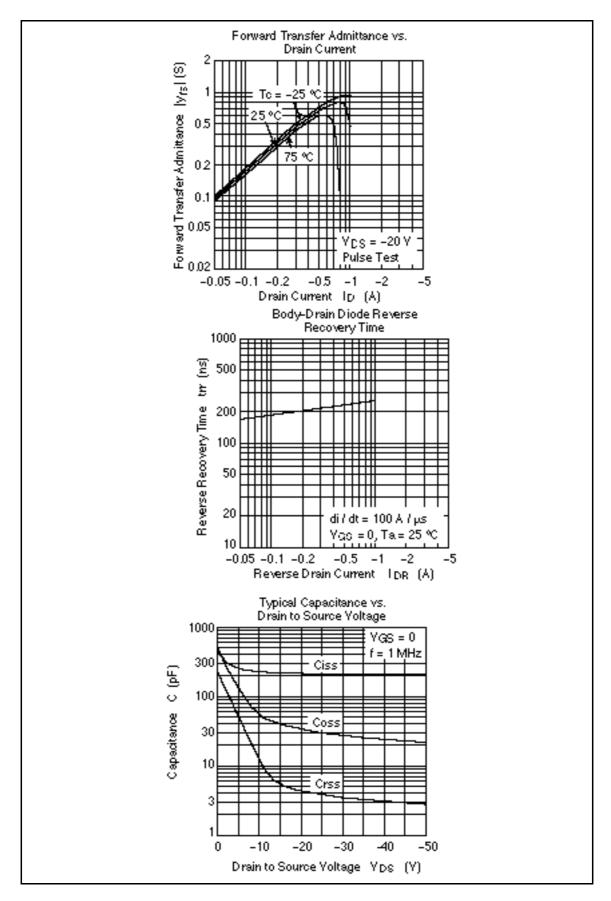
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-600	_	_	V	$I_{D} = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±15	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	-100	μΑ	$V_{DS} = -500 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-2.0	_	-4.0	V	$I_{D} = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Static drain to source on state resistance	$R_{\mathrm{DS(on)}}$	_	15	25		$I_D = -0.3 \text{ A}, V_{GS} = -10 \text{ V}^{*1}$
Forward transfer admittance	y <sub>fs</sub>	0.3	0.45	_	S	$I_D = -0.3 \text{ A}, V_{DS} = -20 \text{ V}^{*1}$
Input capacitance	Ciss	_	220	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	55	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	13	_	pF	_
Turn-on delay time	t <sub>d(on)</sub>	_	7	_	ns	$I_D = -0.3 \text{ A}, V_{GS} = -10 \text{ V},$
Rise time	t <sub>r</sub>	_	20	_	ns	$R_{L} = 100$
Turn-off delay time	t <sub>d(off)</sub>	_	35	_	ns	_
Fall time	t <sub>f</sub>	_	35	_	ns	_
Body to drain diode forward voltage	$V_{DF}$	_	-0.85	_	V	$I_F = -0.5 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t <sub>rr</sub>		230		ns	$I_F = -0.5 \text{ A}, V_{GS} = 0,$ $di_F/dt = 50 \text{ A/}\mu\text{s}$

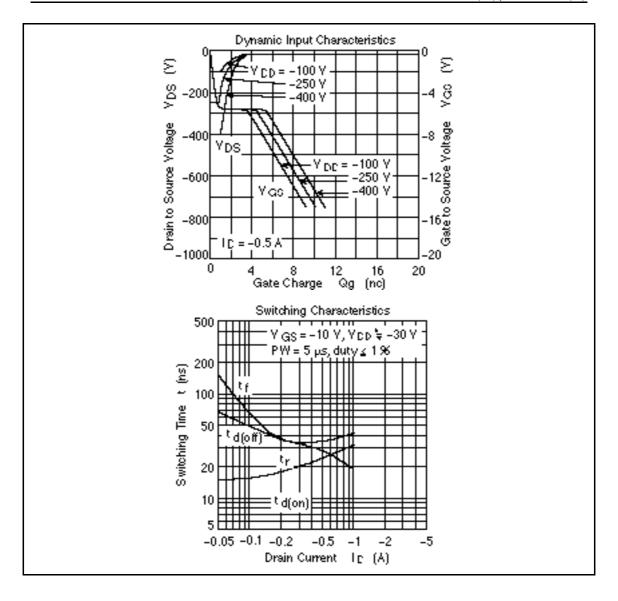
Note: 1. Pulse test

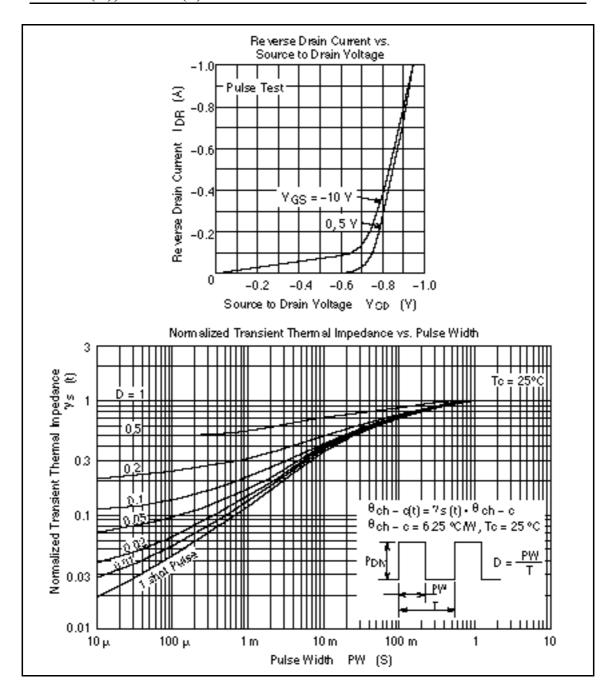


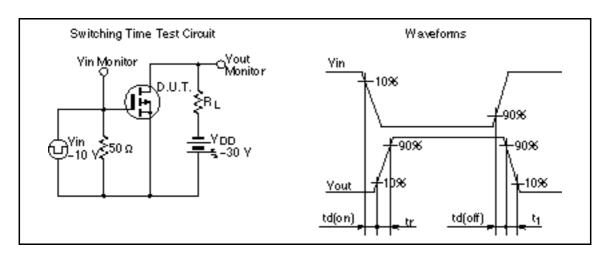












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